BLF7G20L-160P; BLF7G20LS-160P

Power LDMOS transistor

Rev. 01 — 22 June 2010

Objective data sheet

1. Product profile

1.1 General description

160 W LDMOS power transistor for base station applications at frequencies from 1800 MHz to 2000 MHz.

Table 1. Typical performance

Typical RF performance at T_{case} = 25 °C in a common source class-AB production test circuit.

Mode of operation	f	I_{Dq}	V_{DS}	P _{L(AV)}	Gp	η_{D}	ACPR _{400k}	ACPR _{600k}	EVM _{rms}
	(MHz)	(mA)	(V)	(W)	(dB)	(%)	(dBc)	(dBc)	(%)
CW	1805 to 1880	850	28	135	17.5	57	-	-	-
GSM EDGE	1805 to 1880	850	28	65	18.5	43	-61	-74	2.5

1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low R_{th} providing excellent thermal stability
- Designed for broadband operation (1800 MHz to 2000 MHz)
- Lower output capacitance for improved performance in Doherty applications
- Designed for low-memory effects providing excellent digital pre-distortion capability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC

1.3 Applications

 RF power amplifiers for base stations and multi carrier applications in the 1800 MHz to 2000 MHz frequency range



2. Pinning information

Table 2. Pinning

	•			
Pin	Description		Simplified outline	Graphic symbol
BLF7G2	0L-160P (SOT1121A)			
1	drain1			,
2	drain2		1 2 [^{\(\)}]	1
3	gate1			, [-
4	gate2			3 — 5
5	source	<u>[1]</u>	3 4	4—
				2
				sym117

BLF7G2	20LS-160P (SOT1121B)			
1	drain1			,
2	drain2		1 2 [~] [~]	ل.
3	gate1		5	3 📙
4	gate2			5
5	source	<u>[1]</u>	3 4	4
				2 sym117

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Packag	ge	
	Name	Description	Version
BLF7G20L-160P	-	flanged LDMOST ceramic package; 2 mounting holes; 4 leads	SOT1121A
BLF7G20LS-160P	-	earless flanged LDMOST ceramic package; 4 leads	SOT1121B

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+13	V
I _D	drain current		-	<tbd></tbd>	Α
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		-	200	°C

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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	T_{case} = 80 °C; P_L = 100 W	0.41	K/W

6. Characteristics

Table 6. Characteristics

 $T_i = 25$ °C; per section unless otherwise specified.

,						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.9 \text{ mA}$	65	-	-	V
V _{GS(th)}	gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_{D} = 90 \text{ mA}$	1.5	1.9	2.3	V
I _{DSS}	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 28 \text{ V}$	-	-	2	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	14	-	-	Α
I _{GSS}	gate leakage current	$V_{GS} = 11 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	200	nΑ
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 2.5 \text{ A}$	-	<tbd></tbd>	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 3.15 \text{ A}$	-	0.15	-	Ω

7. Test information

Table 7. Application information

f = 1805 MHz and 1880 MHz; RF performance at $V_{DS} = 28$ V; $I_{Dq} = 850$ mA; $T_{case} = 25$ °C; 2 sections combined unless otherwise specified; in a class-AB production test circuit.

Parameter	Conditions	Min	Тур	Max	Unit
peration: GSM EDGE; P _{L(AV)} = 65 W			••		
power gain		17.3	18.5	-	dB
input return loss		-	-15	-8	dB
drain efficiency		40	43	-	%
adjacent channel power ratio (400 kHz)		-	-61	-58	dBc
adjacent channel power ratio (600 kHz)		-	-74	-70.5	dBc
RMS EDGE signal distortion error		-	2.5	3.8	%
peak EDGE signal distortion error		-	8	12.5	%
peration: CW; P _{L(AV)} = 135 W					
power gain		16.8	17.5	-	dB
drain efficiency		52	57	-	%
	power gain input return loss drain efficiency adjacent channel power ratio (400 kHz) adjacent channel power ratio (600 kHz) RMS EDGE signal distortion error peak EDGE signal distortion error peration: CW; P _{L(AV)} = 135 W power gain	power gain input return loss drain efficiency adjacent channel power ratio (400 kHz) adjacent channel power ratio (600 kHz) RMS EDGE signal distortion error peak EDGE signal distortion error peration: CW; P _{L(AV)} = 135 W power gain	power gain 17.3 input return loss drain efficiency 40 adjacent channel power ratio (400 kHz) adjacent channel power ratio (600 kHz) RMS EDGE signal distortion error peak EDGE signal distortion error - peration: CW; P _{L(AV)} = 135 W power gain 16.8	power gain finput return loss drain efficiency adjacent channel power ratio (400 kHz) RMS EDGE signal distortion error peak EDGE signal distortion error peration: CW; P _{L(AV)} = 135 W power gain 17.3 18.5 - 15 40 43 - 61 - 74 RMS EDGE signal distortion error - 2.5 peak EDGE signal distortion error - 8 peration: CW; P _{L(AV)} = 135 W power gain 16.8 17.5	power gain 17.3 18.5 - input return loss15 -8 drain efficiency 40 43 - adjacent channel power ratio (400 kHz)61 -58 adjacent channel power ratio (600 kHz)74 -70.5 RMS EDGE signal distortion error - 2.5 3.8 peak EDGE signal distortion error - 8 12.5 peration: CW; P _{L(AV)} = 135 W power gain 16.8 17.5 -

7.1 Ruggedness in class-AB operation

The BLF7G20L-160P and BLF7G20LS-160P are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: $V_{DS} = 28 \text{ V}$; $I_{Dq} = 850 \text{ mA}$; $P_L = 160 \text{ W}$ (CW); f = 1805 MHz.

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8. Package outline

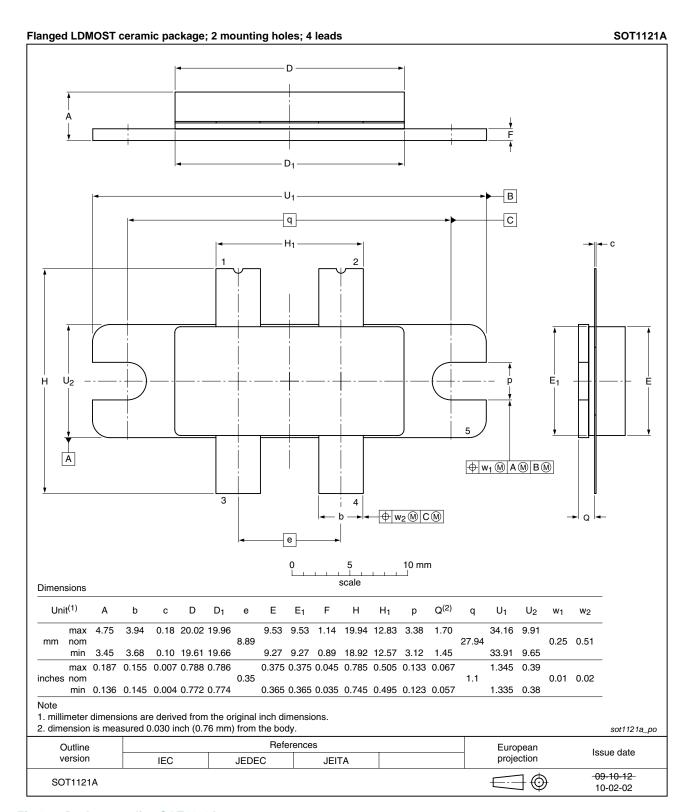


Fig 1. Package outline SOT1121A

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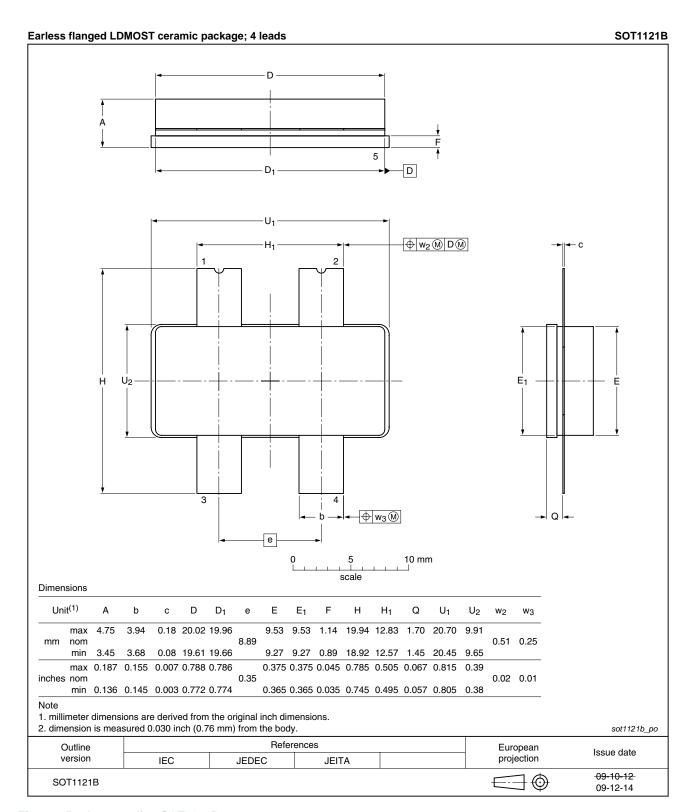


Fig 2. Package outline SOT1121B

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9. Abbreviations

Table 8. Abbreviations

Acronym	Description
CW	Continuous Wave
EDGE	Enhanced Data rates for GSM Evolution
ESD	ElectroStatic Discharge
IS-95	Interim Standard 95
LDMOS	Laterally Diffused Metal Oxide Semiconductor
LDMOST	Laterally Diffused Metal Oxide Semiconductor Transistor
RF	Radio Frequency
SMD	Surface Mounted Device
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

10. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF7G20L-160P_7G20LS-160P v.1	20100622	Objective data sheet	-	-

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